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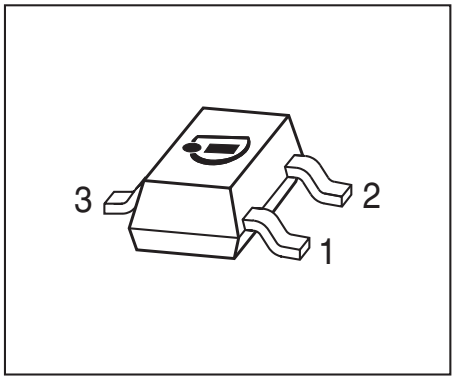
## NPN Silicon Darlington Transistors




- For general AF applications
- High collector current
- High current gain
- Complementary types: BCV26, BCV46 (PNP)
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101

| Type | Marking | Pin Configuration | | | Package |
|---|---|---|---|---|---|
| BCV27 | FFs | 1=B | 2=E | 3=C | SOT23 |
| BCV47 | FGs | 1=B | 2=E | 3=C | SOT23 |

**Maximum Ratings**

| Parameter | Symbol | Value | Unit |
|---|---|---|---|
| Collector-emitter voltage | $V_{CEO}$ | | V |
| BCV27 | | 30 | |
| BCV47 | | 60 | |
| Collector-base voltage | $V_{CBO}$ | | |
| BCV27 | | 40 | |
| BCV47 | | 80 | |
| Emitter-base voltage | $V_{EBO}$ | 10 | |
| Collector current | $I_C$ | 500 | mA |
| Peak collector current, $t_p \leq 10$ ms | $I_{CM}$ | 800 | |
| Base current | $I_B$ | 100 | |
| Peak base current | $I_{BM}$ | 200 | |
| Total power dissipation- $T_S \leq 74$ °C | $P_{tot}$ | 360 | mW |
| Junction temperature | $T_j$ | 150 | °C |
| Storage temperature | $T_{stg}$ | -65 ... 150 | |

## Thermal Resistance

| Parameter | Symbol | Value | Unit |
|---|---|---|---|
| Junction - soldering point[1)] | $R_{thJS}$ | ≤ 210 | K/W |

[1]For calculation of $R_{thJA}$ please refer to Application Note AN077 (Thermal Resistance Calculation)

## Electrical Characteristics at $T_A$ = 25°C, unless otherwise specified

| Parameter | Symbol | Values | | | Unit |
|---|---|---|---|---|---|
| | | min. | typ. | max. | |
| **DC Characteristics** | | | | | |
| Collector-emitter breakdown voltage | $V_{(BR)CEO}$ | | | | - |
| $I_C$ = 10 mA, $I_B$ = 0 , BCV27 | | 30 | - | - | |
| $I_C$ = 10 mA, $I_B$ = 0 , BCV47 | | 60 | - | - | |
| Collector-base breakdown voltage | $V_{(BR)CBO}$ | | | | |
| $I_C$ = 100 µA, $I_E$ = 0 , BCV27 | | 40 | - | - | |
| $I_C$ = 100 µA, $I_E$ = 0 , BCV47 | | 80 | - | - | |
| Emitter-base breakdown voltage | $V_{(BR)EBO}$ | 10 | - | - | V |
| $I_E$ = 10 µA, $I_C$ = 0 | | | | | |
| Collector-base cutoff current | $I_{CBO}$ | | | | µA |
| $V_{CB}$ = 30 V, $I_E$ = 0 , BCV27 | | - | - | 0.1 | |
| $V_{CB}$ = 60 V, $I_E$ = 0 , BCV47 | | - | - | 0.1 | |
| $V_{CB}$ = 30 V, $I_E$ = 0 , $T_A$ = 150 °C, BCV27 | | - | - | 10 | |
| $V_{CB}$ = 60 V, $I_E$ = 0 , $T_A$ = 150 °C, BCV47 | | - | - | 10 | |
| Emitter-base cutoff current | $I_{EBO}$ | - | - | 100 | nA |
| $V_{EB}$ = 4 V, $I_C$ = 0 | | | | | |
| DC current gain[1)] | $h_{FE}$ | | | | - |
| $I_C$ = 100 µA, $V_{CE}$ = 1 V, BCV27 | | 4000 | - | - | |
| $I_C$ = 100 µA, $V_{CE}$ = 1 V, BCV47 | | 2000 | - | - | |
| $I_C$ = 10 mA, $V_{CE}$ = 5 V, BCV27 | | 10000 | - | - | |
| $I_C$ = 10 mA, $V_{CE}$ = 5 V, BCV47 | | 4000 | - | - | |
| $I_C$ = 100 mA, $V_{CE}$ = 5 V, BCV27 | | 20000 | - | - | |
| $I_C$ = 100 mA, $V_{CE}$ = 5 V, BCV47 | | 10000 | - | - | |
| $I_C$ = 0.5 A, $V_{CE}$ = 5 V, BCV27 | | 4000 | - | - | |
| $I_C$ = 0.5 A, $V_{CE}$ = 5 V, BCV47 | | 2000 | - | - | |
| Collector-emitter saturation voltage[1)] | $V_{CEsat}$ | - | - | 1 | V |
| $I_C$ = 100 mA, $I_B$ = 0.1 mA | | | | | |
| Base emitter saturation voltage[1)] | $V_{BEsat}$ | - | - | 1.5 | |
| $I_C$ = 100 mA, $I_B$ = 0.1 mA | | | | | |

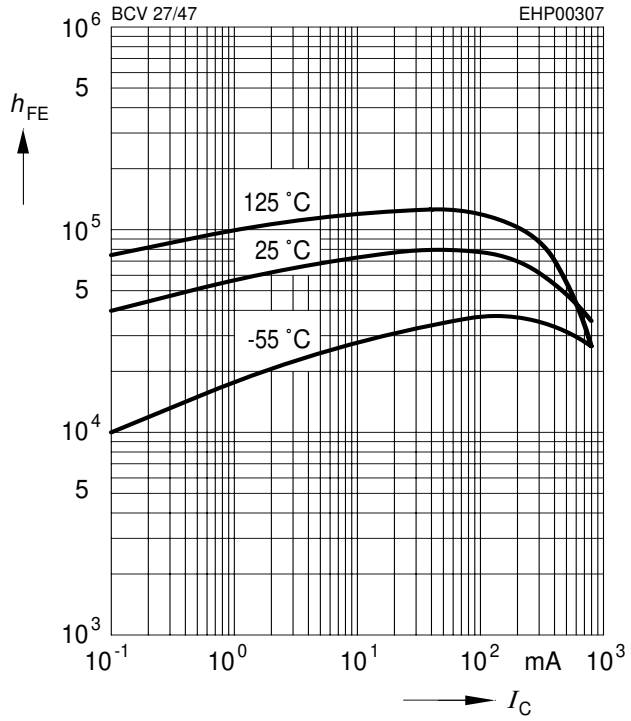
[1]Pulse test: t < 300µs; D < 2%

**Electrical Characteristics** at $T_A$ = 25°C, unless otherwise specified

| Parameter | Symbol | Values | | | Unit |
|---|---|---|---|---|---|
| | | min. | typ. | max. | |
| **AC Characteristics** | | | | | |
| Transition frequency<br>$I_C$ = 50 mA, $V_{CE}$ = 5 V, $f$ = 100 MHz | $f_T$ | - | 170 | - | MHz |
| Collector-base capacitance<br>$V_{CB}$ = 10 V, $f$ = 1 MHz | $C_{cb}$ | - | 3 | - | pF |

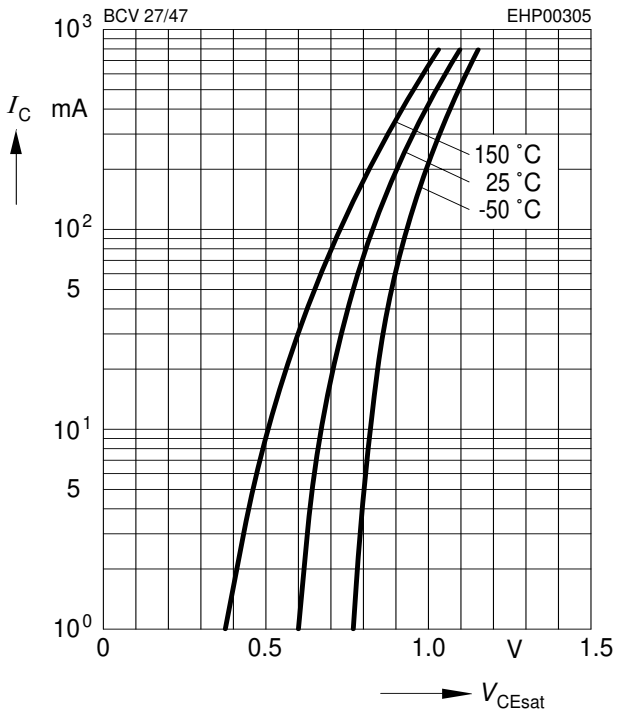
**DC current gain $h_{FE} = f(I_C)$**

$V_{CE}$ = 5 V



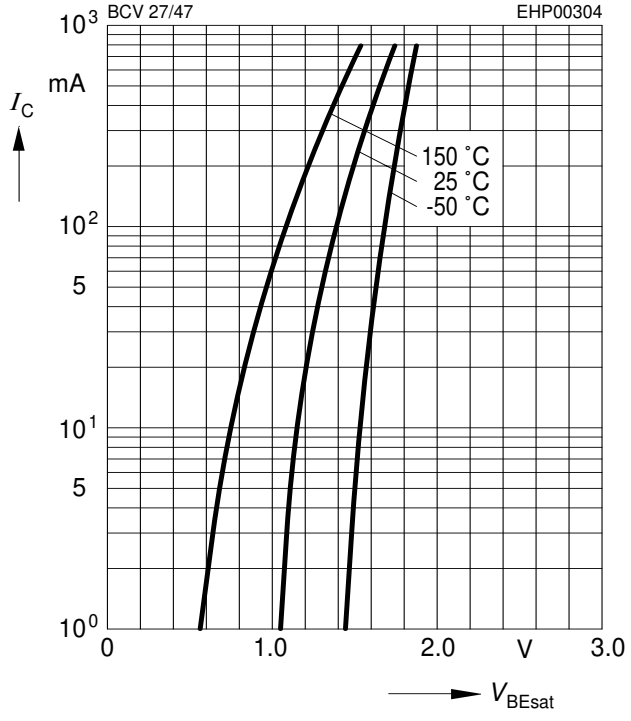

**Collector-emitter saturation voltage**

$I_C = f(V_{CEsat})$, $h_{FE}$ = 10



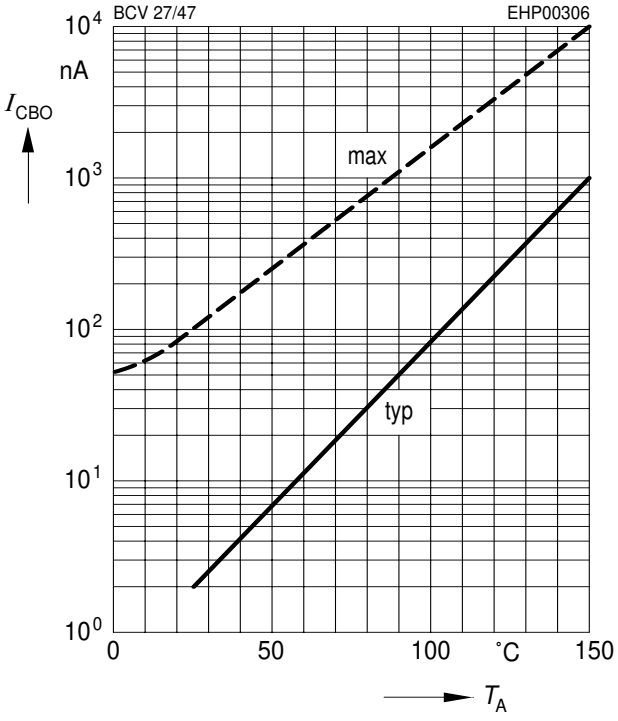

**Base-emitter saturation voltage**

$I_C = f(V_{BEsat})$, $h_{FE}$ = 10



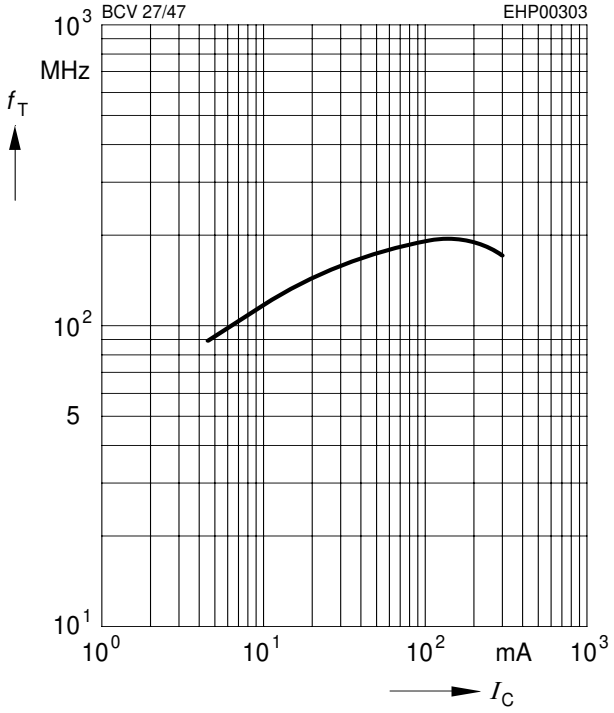

**Collector cutoff current $I_{CBO} = f(T_A)$**

$V_{CB} = V_{CEmax}$



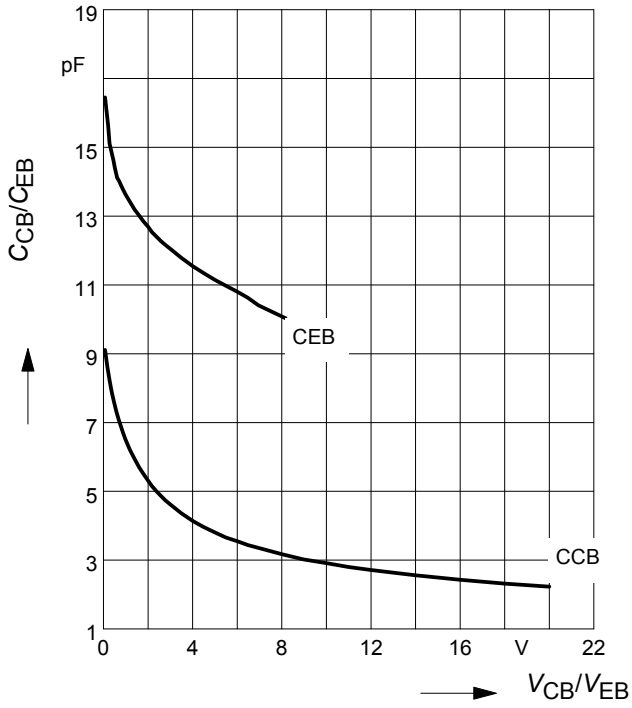
**Transition frequency $f_T = f(I_C)$**

$V_{CE}$ = 5 V

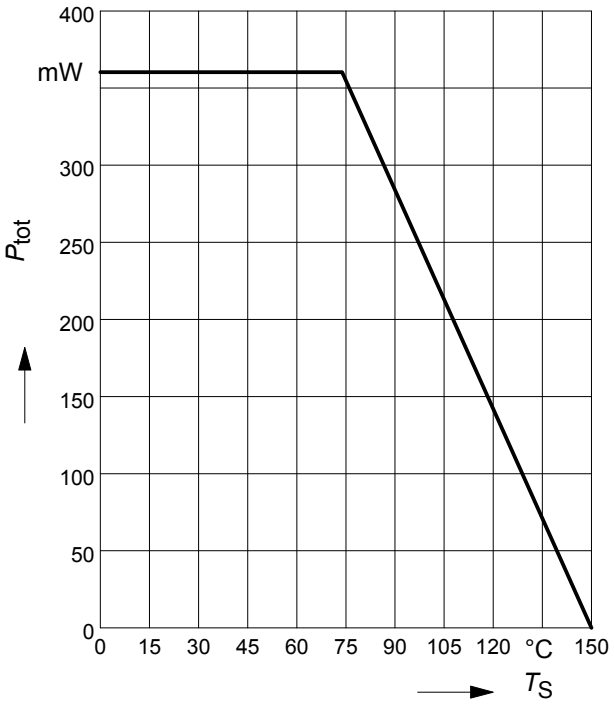



**Collector-base capacitance $C_{cb} = f(V_{CB})$**

**Emitter-base capacitance $C_{eb} = f(V_{EB})$**

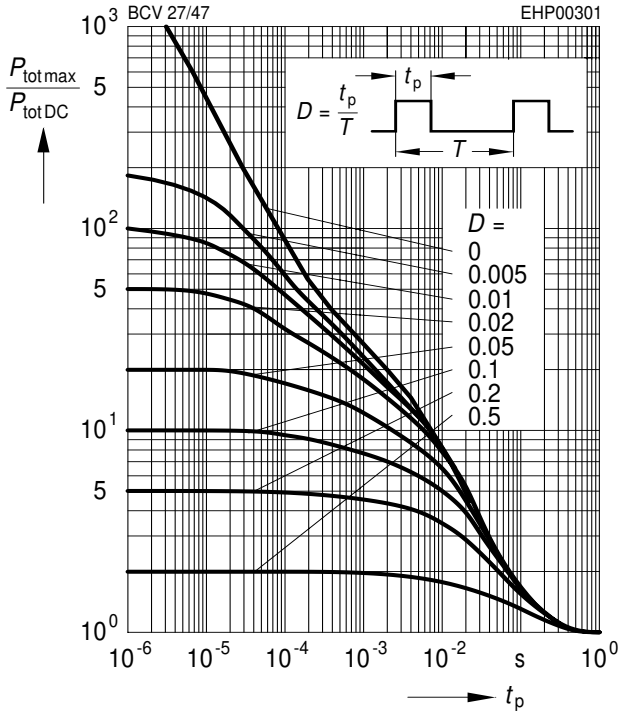



**Total power dissipation $P_{tot} = f(T_S)$**

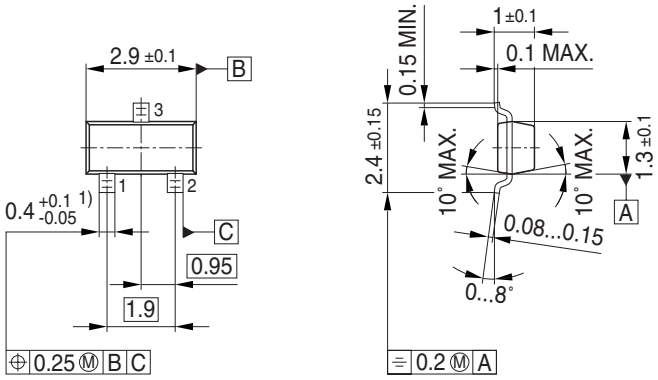



**Permissible Pulse Load**

$P_{totmax}/P_{totDC} = f(t_p)$

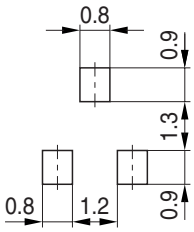


## Package Outline

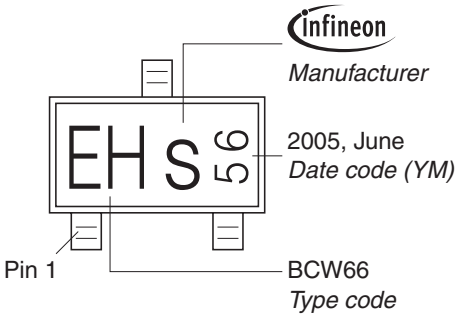



1) Lead width can be 0.6 max. in dambar area

## Foot Print

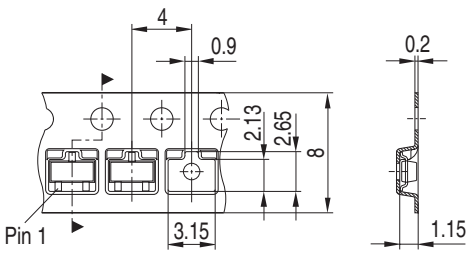



## Marking Layout (Example)




## Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel
Reel ø330 mm = 10.000 Pieces/Reel



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